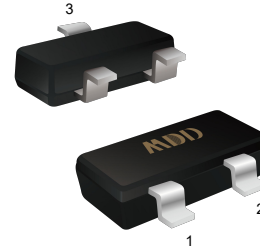


$V_{(BR)DSS}$	$R_{DS(on)Typ}$	$I_D Max$
-20V	37mΩ@ -4.5V	-4.8A
	43mΩ@ -3.3V	



1. Gate
2. Source
3. Drain

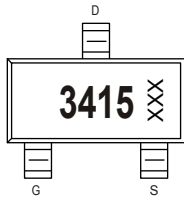
FEATURE

- Excellent $R_{DS(ON)}$, low gate charge, low gate voltages

Application

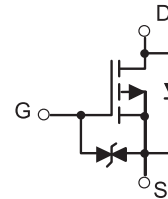
- Load/Power Switching
- Interfacing Switching

MARKING



XXX:Date Code

Equivalent circuit



Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{(BR)DSS}$	-20	V	
Gate-Source Voltage	V_{GS}	±8		
Continuous Drain Current	I_D	$T_A = 25^\circ C$	-4.8	A
		$T_A = 70^\circ C$	-3.6	
Pulsed Drain Current ¹⁾	I_{DM}	-30	A	
Maximum Power Dissipation ²⁾	P_D	$T_A = 25^\circ C$	1.5	W
		$T_A = 70^\circ C$	1.0	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-50 to 150	°C	
Junction-to-Ambient Thermal Resistance (PCB mounted) ²⁾	R_{thJA}	80	°C/W	

Notes

- ¹⁾ Pulse width limited by maximum junction temperature.
- ²⁾ Surface Mounted on FR4 Board, $t \leq 5$ sec.

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static Parameters						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.7	-1.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V (TA=25^\circ C)$			-1	μA
		$V_{DS} = 16V, V_{GS} = 0V (TA=125^\circ C)$			-100	
Gate-body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 10	
Drain-source on-state resistance(note1)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4A$		37	45	m Ω
		$V_{GS} = -3.3V, I_D = -3A$		43	55	
		$V_{GS} = -2.5V, I_D = -2A$		52	65	
Forward transconductance(note2)	g_{FS}	$V_{DS} = -5V, I_D = -4A$	8			S
Dynamic Parameters (note3)						
Input capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		675		pF
Output capacitance	C_{oss}			120		
Reverse transfer capacitance	C_{rss}			85		
Gate resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		6.5		Ω
Switching Parameters						
Total gate charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -4A$		14.2		nC
Gate-Source charge	Q_{gs}			3.2		
Gate-drain charge	Q_{gd}			5.8		
Turn-on delay time (note3)	$t_{d(on)}$	$V_{DS} = -10V, V_{GS} = -4.5V$ $R_{GEN} = 3\Omega, R_L = 2.5\Omega,$		15		ns
Turn-on rise time(note3)	t_r			11		
Turn-off delay time(note3)	$t_{d(off)}$			22		
Turn-off fall time(note3)	t_f			35		
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^\circ C$			-2.0	A
Body diode voltage (note 2)	V_{SD}	$I_S = -2A, V_{GS} = 0V$		-0.83	-1.2	V

Notes:

- 1) PRRepetitive rating, pulse width limited by junction temperature.
- 2) Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 3) These parameters have no way to verify.

Typical Characteristics

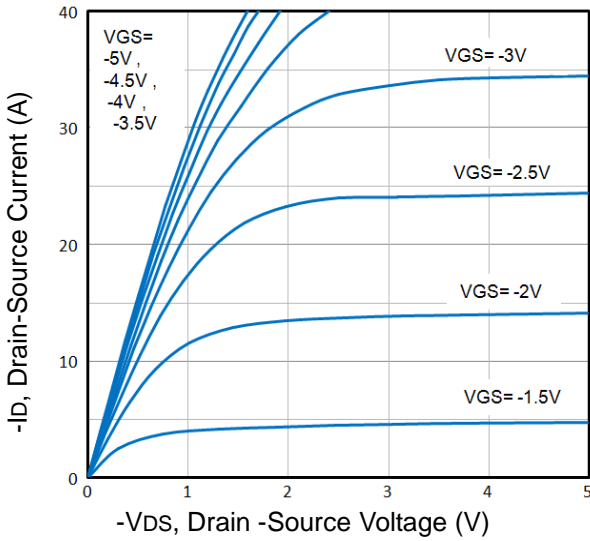


Fig1. Typical Output Characteristics

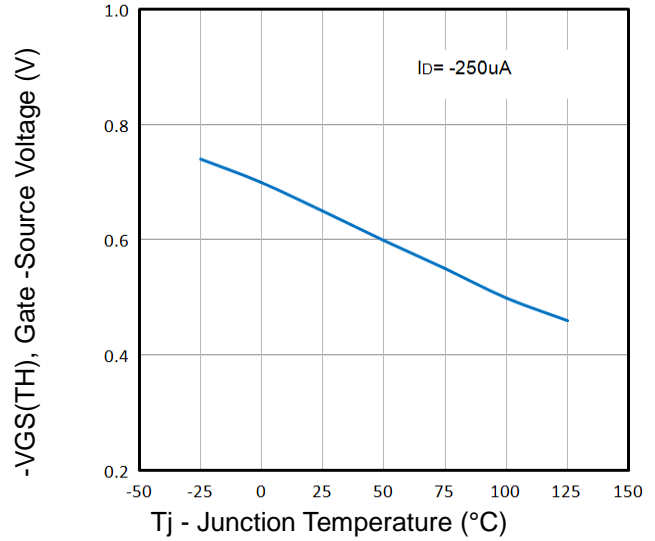


Fig2. Normalized Threshold Voltage Vs. Temperature

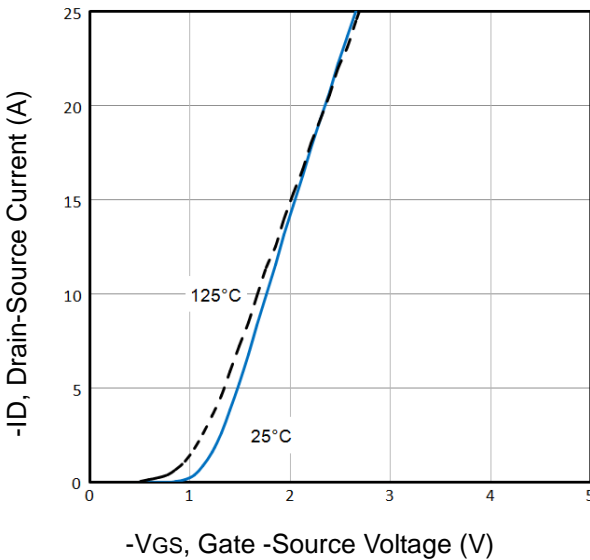


Fig3. Typical Transfer Characteristics

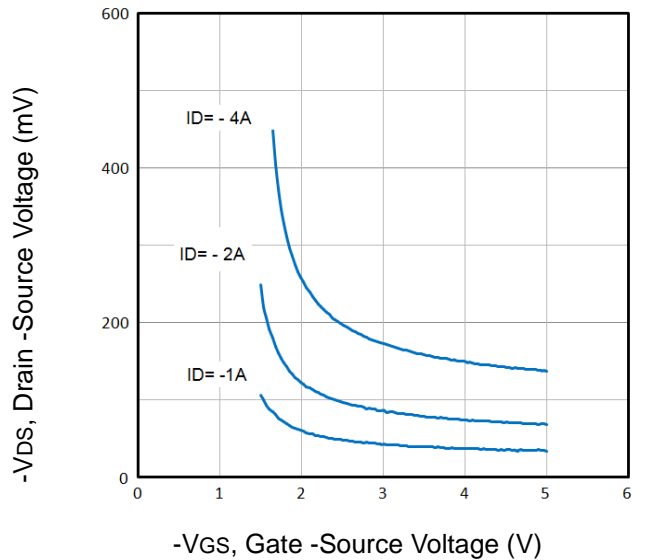


Fig4. Drain-Source Voltage vs Gate-Source Voltage

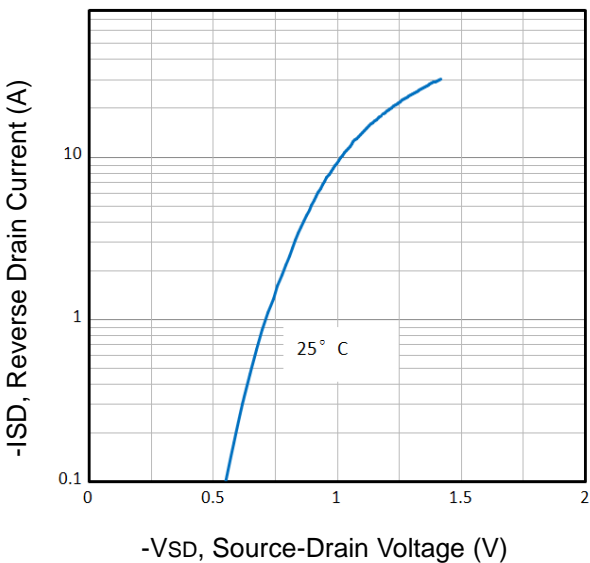


Fig5. Typical Source-Drain Diode Forward Voltage

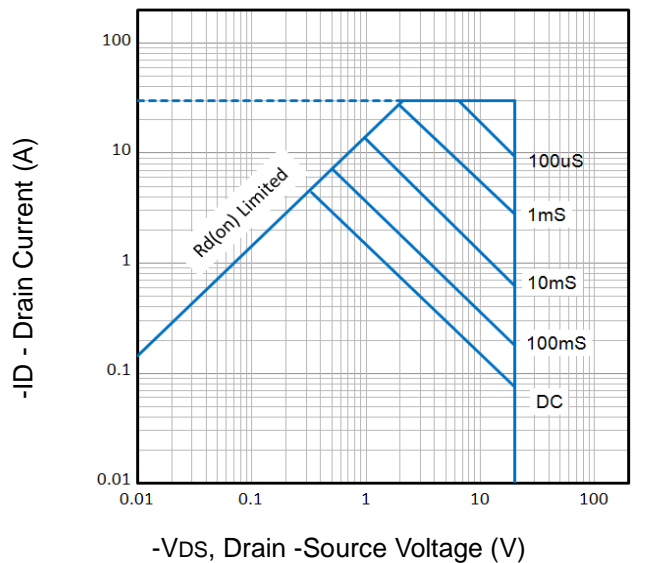


Fig6. Maximum Safe Operating Area

Typical Characteristics

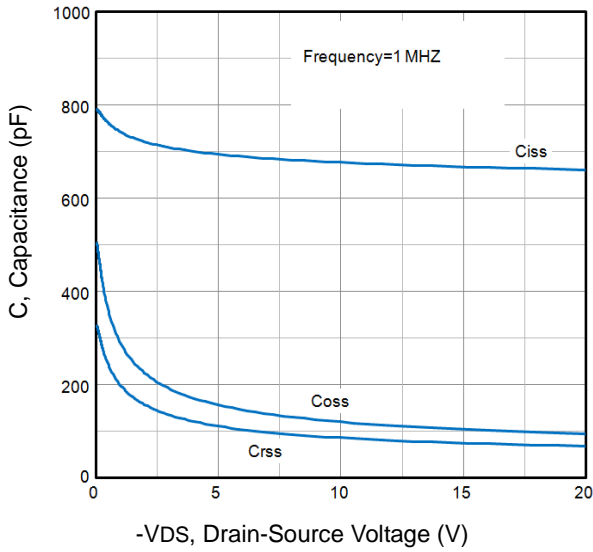


Fig7. Typical Capacitance Vs. Drain-Source Voltage

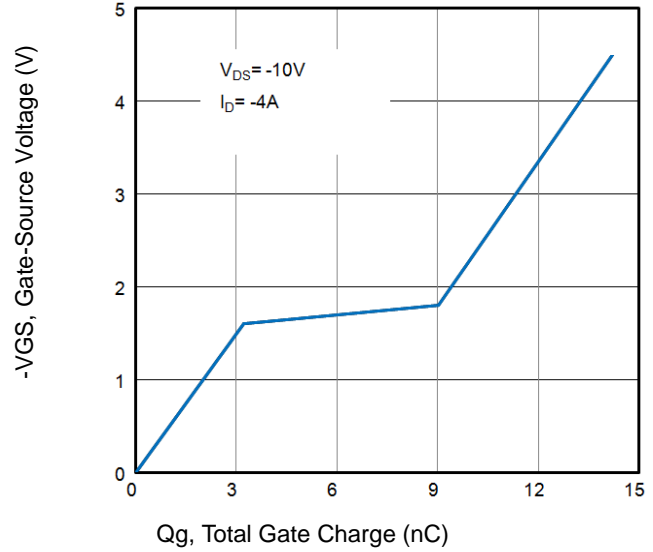


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

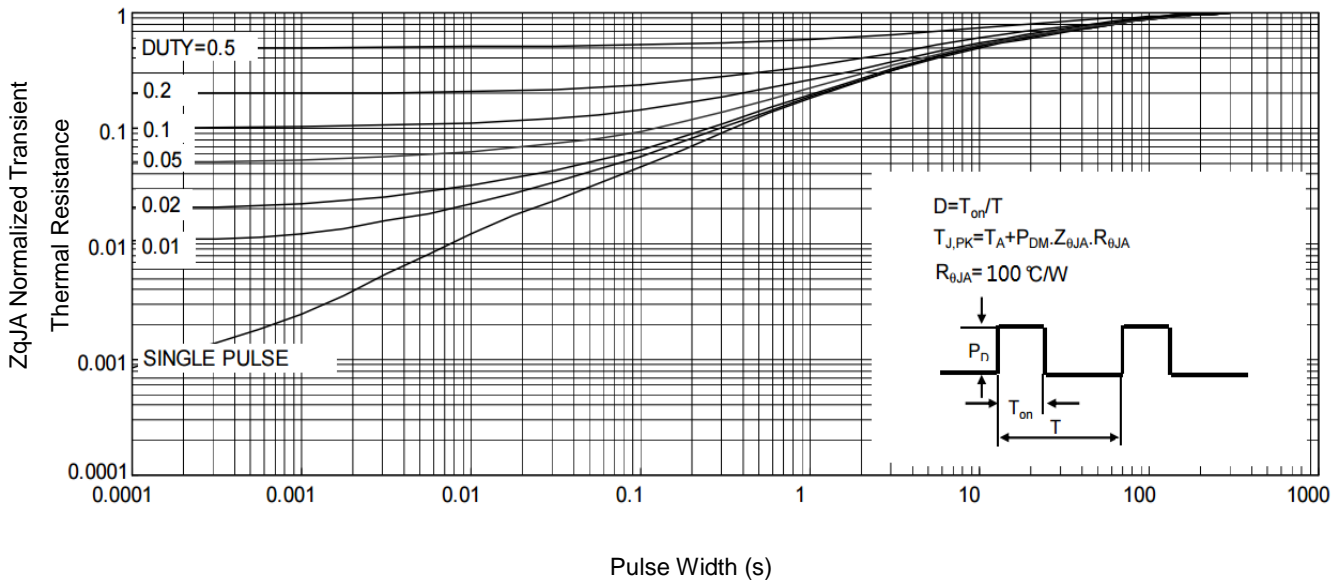


Fig9. Normalized Maximum Transient Thermal Impedance

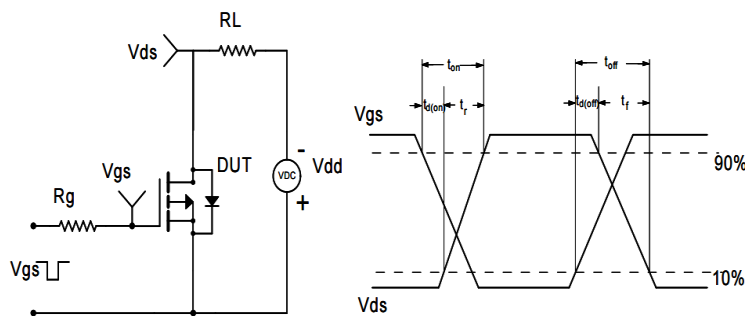
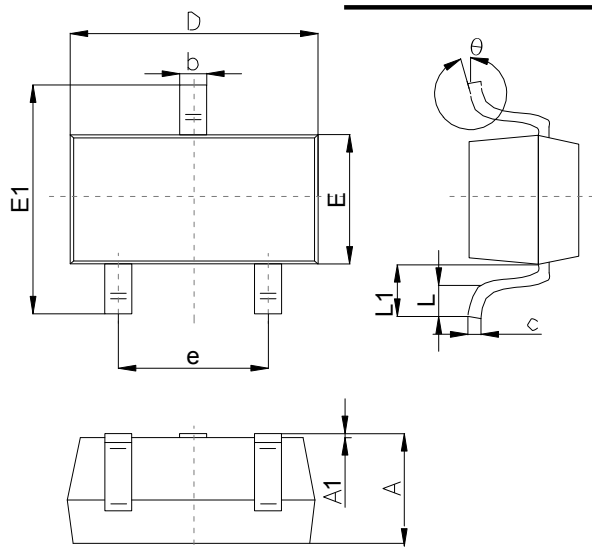


Fig10. Switching Time Test Circuit and waveforms

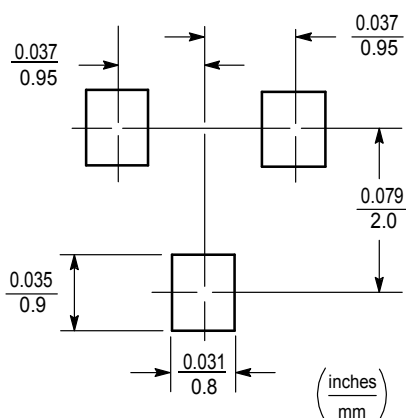
Outlitne Drawing

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	0.65		1.40
A1	0.00		0.20
b	0.30		0.55
c	0.08		0.20
D	2.70		3.10
E	1.15		1.65
E1	2.10		2.80
e	1.70		2.10
L	0.15		0.50
L1	0.35		0.70
θ	0°		12°

Suggested Pad Layout



Note:

1. Controlling dimension:in/millimeters.
- 2.General tolerance: ±0.05mm.
- 3.The pad layout is for reference purposes only.